

Docket No.: IN-1078



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By:

Date: December 30, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/901,526 Confirmation No: 7099
Applicant : Matthias Förster, et al.
Filed : July 9, 2001
Title : Process for Producing a Microroughness on a Surface
Art Unit : 2812
Examiner : Savitri Mulpuri

Docket No. : IN-1078
Customer No. : 24131

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. 1.97(d)

Hon. Commissioner for Patents
Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are cited herewith:

United States Patent No. 5,554,557 (Koh), dated September 10, 1996;

United States Patent No. 5,290,729 (Hayashide, et al.), dated March 1, 1994;

European Patent Application EP 0 448 374 A1 (Watanabe, et al.), dated September 25, 1991;

Hayashide, et al.: "Fabrication of Storage Capacitance-Enhanced Capacitors with a Rough Electrode", Japanese Journal of Applied Physics, Tokyo, JP, 1990, XP 000178146, pp. 869-872;

Yoshimaru, et al.: "Rugged Surface Poly-Si Electrode and Low Temperature Deposited Si₃N₄ for 64Mbit and Beyond STC DRAM Cell", 1990 IEEE, XP 10554581A, pp. 659-662;

European Search Report dated October 31, 2005.


In accordance with 37 C.F.R. 1.97(e) the undersigned herewith states that each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

In accordance with 37 C.F.R. 1.97 (e), consideration of this Information Disclosure Statement is requested.

Enclosed is the fee in the amount of \$180.00.

Respectfully submitted,



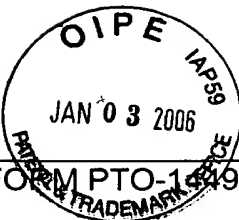
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FORM PTO-1549 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: Applic. No. IN-1078 09/901,526 Applicant Matthias Förster, et al. Filing Date Group Art Unit July 9, 2001 2812			
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,554,557	9/1996	Koh			
	B	5,290,729	3/1994	Hayashide, et al.			
	C						
	D						
	E						
	F						
	G						
	H						
	I						
FOREIGN PATENT DOCUMENT							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES / NO
	J	0 448 374 A1	9/1991	Europe			
	K						
	L						
	M						
	N						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
	O	Hayashide, et al.: "Fabrication of Storage Capacitance-Enhanced Capacitors with a Rough Electrode", Japanese Journal of Applied Physics, Tokyo, JP, 1990, XP 000178146, pp. 869-872					
	P	Yoshimaru, et al.: "Rugged Surface Poly-Si Electrode and Low Temperature Deposited Si ₃ N ₄ for 64Mbit and Beyond STC DRAM Cell", 1990 IEEE, XP 10554581A, pp. 659-662					
EXAMINER				DATE CONSIDERED			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							